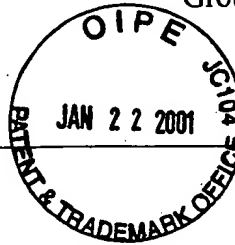


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Hsiao, Tommy C.; Hui, Angela T.; Ogle, Robert B.; Pham, Tuan Duc;  
Plat, Marina V.; Ramsbey, Mark T.; Shen, Lewis  
Assignee: Advanced Micro Devices, Inc.  
Title: Polished Flash Process With Metal Gates And Improved Planarity  
Serial No.: 09/430,366 Filing Date: October 28, 1999  
Examiner: J. Chen Group Art Unit: 2813  
Docket No.: M-7523 US



San Jose, California  
January 16, 2001

COMMISSIONER FOR PATENTS  
Washington, D. C. 20231

AMENDMENT

Dear Sir:

This submission responds to the Office Action of July 7, 2000. Applicants amend the above-referenced patent application as follows:

IN THE CLAIMS

Please cancel Claim 13.

Please amend Claims 1-5 and 7-11 as follows:

1. (Amended) A method of making a flash memory cell including a substrate [having] and a floating gate [of a first thickness], the method comprising:

forming an oxide on exposed surfaces of the floating gate; → *NOT shown in drawing*

depositing an insulator layer on the substrate[, the insulator covering] and the floating gate, the insulator layer being deposited to a thickness greater than a thickness

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